10/676738

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/676738	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:04
L2	9	(reducing adj2 height) and smoothing and medium and roughness and solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:41
L3	48	(reducing adj2 height) and (smoothing aadj medium) and roughness and solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:07
L4	1	(reducing adj2 height) and (smoothing adj medium) and roughness and solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:15
L5	1	("6811855").PN.	USPAT	OR	OFF	2006/05/03 14:15
L6	1	("6602620").PN.	USPAT	OR	OFF	2006/05/03 14:15
L7	1	("5479311").PN.	USPAT	OR	OFF	2006/05/03 14:16
L8	1	5 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:22
L9	1	"6686024".PN.	USPAT; USOCR	OR	ON	2006/05/03 14:18
L10	1	"6506486".PN.	USPAT; USOCR	OR	ON	2006/05/03 14:18
L11	1	"20030054201".PN.	US-PGPUB	OR	ON	2006/05/03 14:18
L12	1	11 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:22
L13	1	("6602620").PN.	USPAT	OR	OFF	2006/05/03 14:22

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L14	1	13 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:27
L15	1	"6271994".PN.	USPAT; USOCR	OR	ON	2006/05/03 14:23
L16	1	"6183832".PN.	USPAT; USOCR	OR	ON	2006/05/03 14:23
L17	1	15 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:31
L18	1	"5901001".PN.	USPAT; USOCR	OR	ON	2006/05/03 14:30
L19	1	18 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:33
L20	1	16 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:34
L21	. 1	("5479311").PN.	USPAT	OR	OFF	2006/05/03 14:34
L22	1	21 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:43
L23	1	(reducing adj2 height) and (smoothing adj medium) and (roughness adj formation) and solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:39
L24	1	(reducing adj2 height) and (roughness adj formation) and solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:39

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L25	1	(reducing adj2 height) and (smoothing adj medium) and rough and plurality and solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:40
L26	9	(reducing adj2 height) and smoothing and medium and roughness and solvent and surface and plurality	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:43
L27	1	("6106927").PN.	USPAT	OR	OFF	2006/05/03 14:43
L28	1	27 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:49
L29	1	"5141778".PN.	USPAT; USOCR	OR	ON	2006/05/03 14:44
L30	1	29 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:56
L31	1	("4567066").PN.	USPAT	OR	OFF	2006/05/03 14:49
L32	1	31 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 14:49
L33	1	("6764800").PN.	USPAT	OR	OFF	2006/05/03 14:56
L34	1	33 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:08
L35	1	("6656748").PN.	USPAT	OR	OFF	2006/05/03 14:59
L36	1	35 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/05/03 15:00

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L37	1	"6258698".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:04
L38	1	"6221738".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:04
L39	1	"6190937".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:05
L40	1	"6143628".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:05
L41	1	"6140209".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:05
L42	1	"6121112".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:05
L43	1	"6100165".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:06
L44	1	"5856229".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:06
L45	1	"5559043".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:06
L46	1	"5453394".PN.	USPAT; USOCR	OR	ON	2006/05/03 15:07
L47	1	"5371037".PN.	USPAT; USOCR	OR ·	ON	2006/05/03 15:07
L48	1	("5856229").PN.	USPAT	OR	OFF	2006/05/03 15:08
L49	, 1	48 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:09
L50	. 1	("6428396").PN.	USPAT	OR	OFF	2006/05/03 15:09
L51	1	50 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:10
L52	48	3 and (smooth or roughness or rough or polymer or height or surface or formation or reduce or reducing or wafer or semiconductor or plurlity or expose or exposure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:24

L53	2939	438/3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:24
L54	2766	438/197	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:24
L55	3899	438/622	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25
L56	1425	438/648	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25
L57	1562	438/680	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25
L58	1051	438/688	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25
L59	1288	438/685	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25
L60	1196	438/683	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25

L61	807	438/678	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25
L62	1065	438/712	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25
L63	2015	438/745	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/03 15:25
L64	1169	438/738	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/05/03 15:25